

# Supporting Information for

## A High-voltage Solar Rechargeable Device Based on a CoPi/BiVO<sub>4</sub> Faradaic Junction

Junzhe Zhang<sup>1 †</sup>, Dongjian Jiang<sup>1 †</sup>, Pin Wang<sup>2</sup>, Jun Zhong<sup>3</sup>, Gengzhi Sun<sup>4</sup>, Yingfang Yao<sup>1</sup>, Wenjun Luo<sup>1\*</sup>, Zhigang Zou<sup>1,2</sup>

<sup>1</sup>National Laboratory of Solid State Microstructures, College of Engineering and Applied Sciences, Nanjing University, Nanjing 210093, China

<sup>2</sup>Eco-materials and Renewable Energy Research Center (ERERC), Jiangsu Key Laboratory for Nano Technology, National Laboratory of Solid State Microstructures and Department of Physics, Nanjing University, Nanjing 210093, China

<sup>3</sup>Institute of Functional Nano and Soft Materials Laboratory (FUNSOM), Jiangsu Key Laboratory for Carbon-Based Functional Materials & Devices, Soochow University, Suzhou 215123, China

<sup>4</sup>Key Laboratory of Flexible Electronics (KLOFE) & Institute of Advanced Materials (IAM), Nanjing Tech University, Nanjing 211816, China

<sup>†</sup>These authors contributed equally to this work. \*Email: wjluo@nju.edu.cn;

### Experimental section

#### Preparation of BiVO<sub>4</sub> electrode

Following previous method <sup>[1]</sup>, Bi layers were firstly electro-deposited on FTO substrates in 20 mM Bi(NO<sub>3</sub>)<sub>3</sub>·5H<sub>2</sub>O ethylene glycol solution. The deposition was carried out by i-t method at the potential of -1.8 V vs. Ag/AgCl and the deposition charge was 300 mC/cm<sup>2</sup>. After electrodeposition, the Bi films were washed by ethanol and dried in air. And then 150 mM VO(acac)<sub>2</sub> in DMSO was dropped on the surface of Bi electrodes, which were calcined in a muffle furnace at 450 °C for 2 hours in air (heating rate = 2 °C/min). In the muffle furnace, Bi and VO<sup>2+</sup> were oxidized and reacted with each other to form BiVO<sub>4</sub>. Finally, residual V<sub>2</sub>O<sub>5</sub> in the BiVO<sub>4</sub> films was removed by soaking the samples in 1 M NaOH aqueous solution for 30 minutes.

### **Preparation of CoPi, CoO<sub>x</sub>H<sub>y</sub>, Co(OH)<sub>2</sub> and Co<sub>3</sub>O<sub>4</sub>**

CoPi samples were electro-deposited on FTO substrates at the potential of 1.1 V vs. Ag/AgCl in 1 M potassium phosphate buffer (pH=7) solution with adding 0.5 mM Co(NO<sub>3</sub>)<sub>2</sub> and the deposition charge was 100 mC/cm<sup>2</sup>. CoO<sub>x</sub>H<sub>y</sub> samples were electro-deposited on FTO substrates at the potential of -0.8 V vs. Ag/AgCl in 0.1 M Co(NO<sub>3</sub>)<sub>2</sub> aqueous solution and the deposition charge was 100 mC/cm<sup>2</sup>. Then CoO<sub>x</sub>H<sub>y</sub> film was oxidized at the potential of 1.2 V vs. Ag/AgCl in 0.5 M Na<sub>2</sub>SO<sub>4</sub> aqueous solution for 1 minute. Co(OH)<sub>2</sub> samples were grown on FTO substrates by chemical bath deposition method at 100 °C for 12 hours. The precursor solution was 0.1 M Co(NO<sub>3</sub>)<sub>2</sub> and 0.5 M CO(NH<sub>2</sub>)<sub>2</sub> aqueous solution. In order to obtain Co<sub>3</sub>O<sub>4</sub>, the as-grown Co(OH)<sub>2</sub> films were annealed in a muffle furnace at 500 °C in air for 5 minutes.

### **Preparation of CoPi/BiVO<sub>4</sub> and CoO<sub>x</sub>H<sub>y</sub>/BiVO<sub>4</sub>**

The CoPi and CoO<sub>x</sub>H<sub>y</sub> were electro-deposited on BiVO<sub>4</sub> on the same conditions as on FTO substrates as mentioned above, but the deposition charge was 20 mC/cm<sup>2</sup>.

### **Assembly of solar rechargeable devices**

CoPi/BiVO<sub>4</sub> or CoO<sub>x</sub>H<sub>y</sub>/BiVO<sub>4</sub> were used as photoelectrodes and commercial carbon cloth (Taiwan Carbon Energy Technology, W0S1002) was used as counter electrode. The electrolytes were 1 M potassium phosphate buffer solution (pH=7) and 0.5 M Na<sub>2</sub>SO<sub>4</sub> aqueous solution, respectively. The two solar rechargeable devices were marked as BiVO<sub>4</sub>/CoPi/KPi<sub>(aq)</sub>/C and BiVO<sub>4</sub>/CoO<sub>x</sub>H<sub>y</sub>/Na<sub>2</sub>SO<sub>4(aq)</sub>/C, respectively.

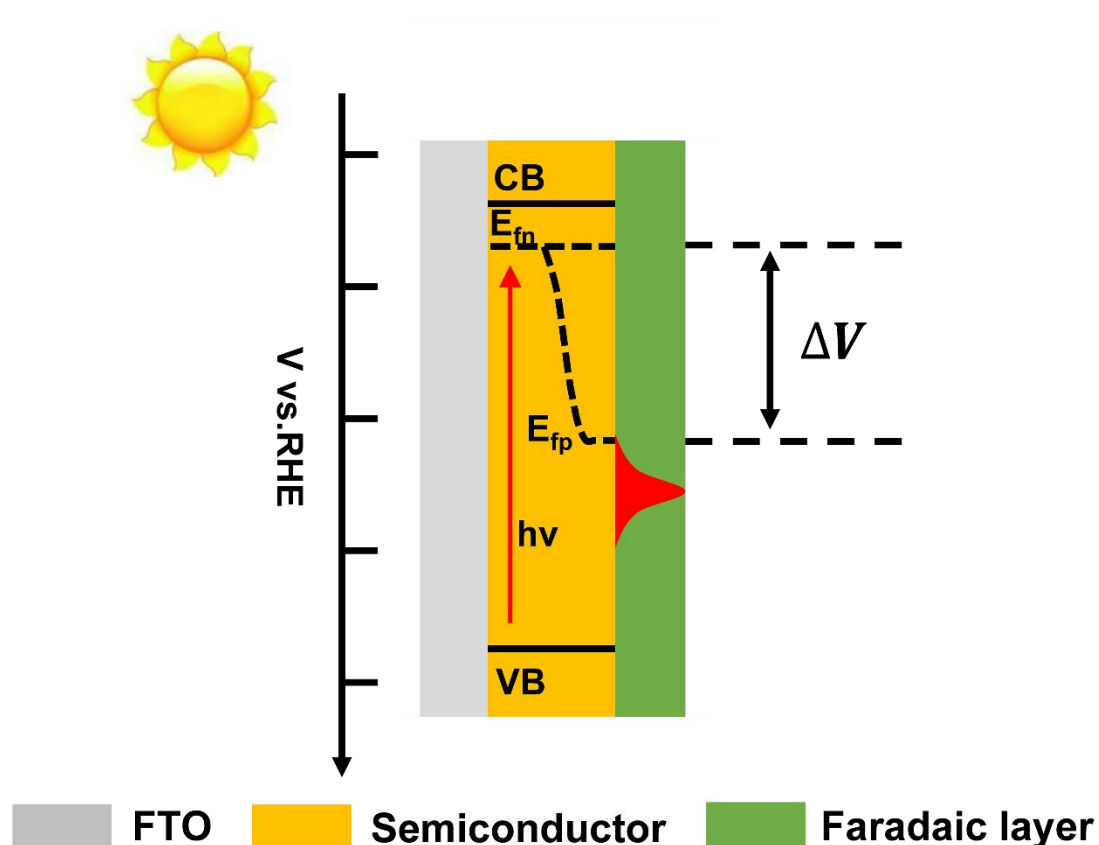
### **Characterizations of samples**

The morphologies of the samples were characterized by SEM (ZEISS Gemini 300) with an accelerating voltage of 10 kV. The TEM (JEOL JEM-2100), XRD (ARL X'TRA) and Raman spectroscopy (Horiba T64000, excitation ~ 488 nm) were employed to investigate the structures of the samples. The absorbance of the samples was measured by ultraviolet-visible-near infrared spectroscopy (UV-Vis-NIR, PE Lambda 950). The chemical valence of the samples was characterized by X-ray photoelectron spectroscopy (XPS, PHI5000 Versa Probe). The binding energies were calibrated by the C1s peak at 284.6 eV. X-ray absorption spectroscopy (XAS) experiments were performed at the National Synchrotron Radiation Laboratory (NSRL, Beamlines MCD-

A and MCD-B (Soochow Beamline for Energy Materials).

### Electrochemical and photoelectrochemical measurements

The electrochemical and photoelectrochemical properties of the samples were measured in a three-electrode system. A Pt electrode and Ag/AgCl were used as a counter electrode and a reference electrode, respectively. For CoPi/FTO and CoPi/BiVO<sub>4</sub> samples, 1 M potassium phosphate buffer solution (pH=7) was used as electrolyte. For CoO<sub>x</sub>H<sub>y</sub>/FTO, CoO<sub>x</sub>H<sub>y</sub>/BiVO<sub>4</sub>, Co(OH)<sub>2</sub>/FTO and Co<sub>3</sub>O<sub>4</sub>/FTO, 0.5 M Na<sub>2</sub>SO<sub>4</sub> aqueous solution was used as electrolyte. The performance of solar rechargeable devices was measured by using a two-electrode system. All electrochemical and photoelectrochemical curves were recorded by the electrochemical workstation (CHI 760e, Shanghai Chenhua). An AM1.5 sunlight simulator with the intensity of 100 mW cm<sup>-2</sup> was used as the light source.



**Figure S1.** Schematic diagram of photovoltage in a Faradaic junction.

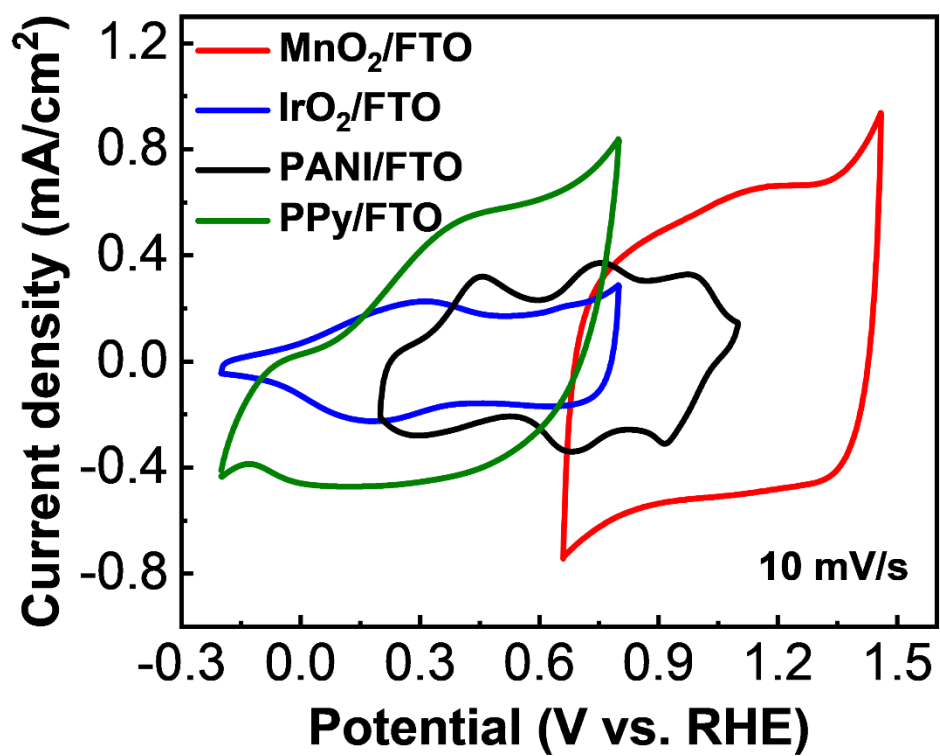


Figure S2. Potential windows of some conventional Faradaic materials.

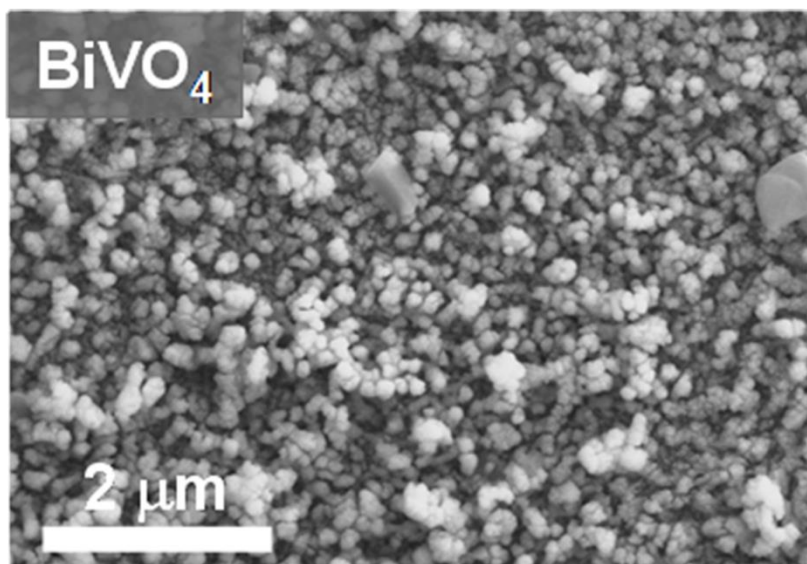


Figure S3. SEM image of bare BiVO<sub>4</sub> on a FTO substrate.

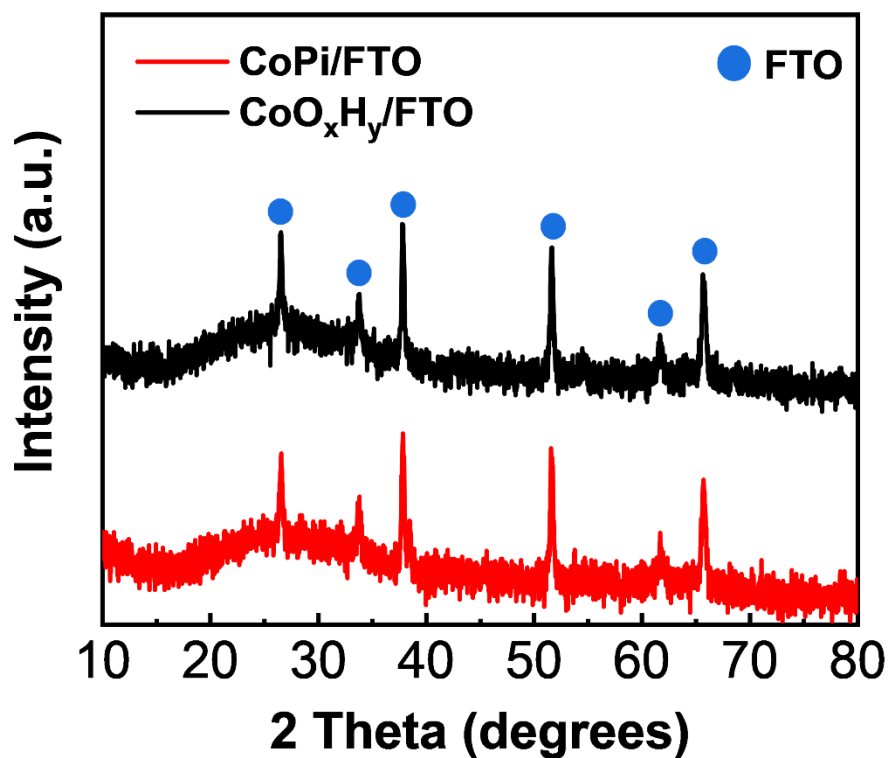


Figure S4. XRD patterns of CoPi/FTO and CoO<sub>x</sub>H<sub>y</sub>/FTO.

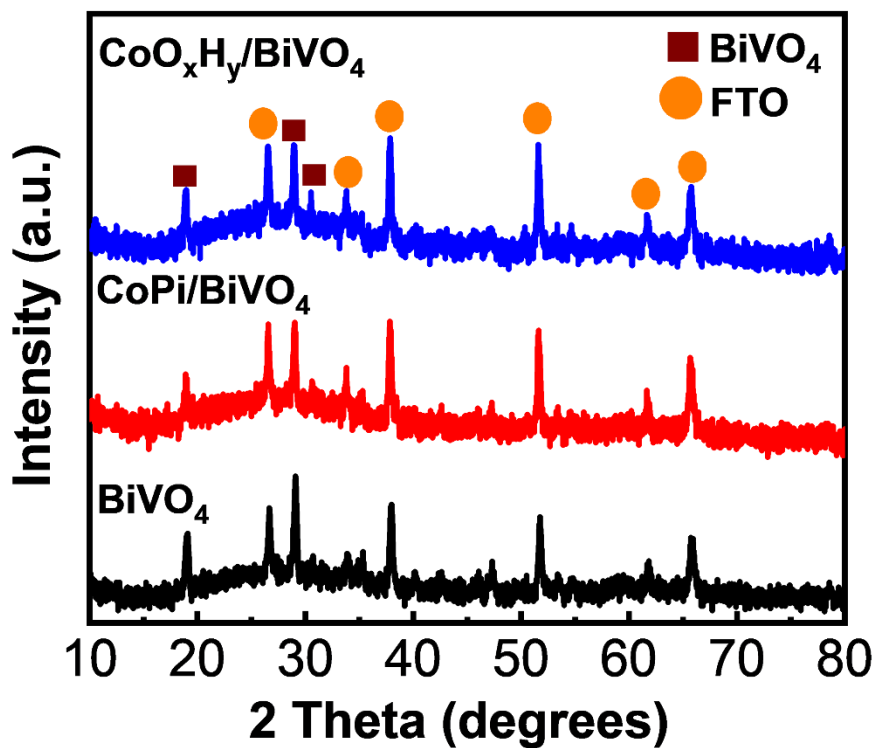
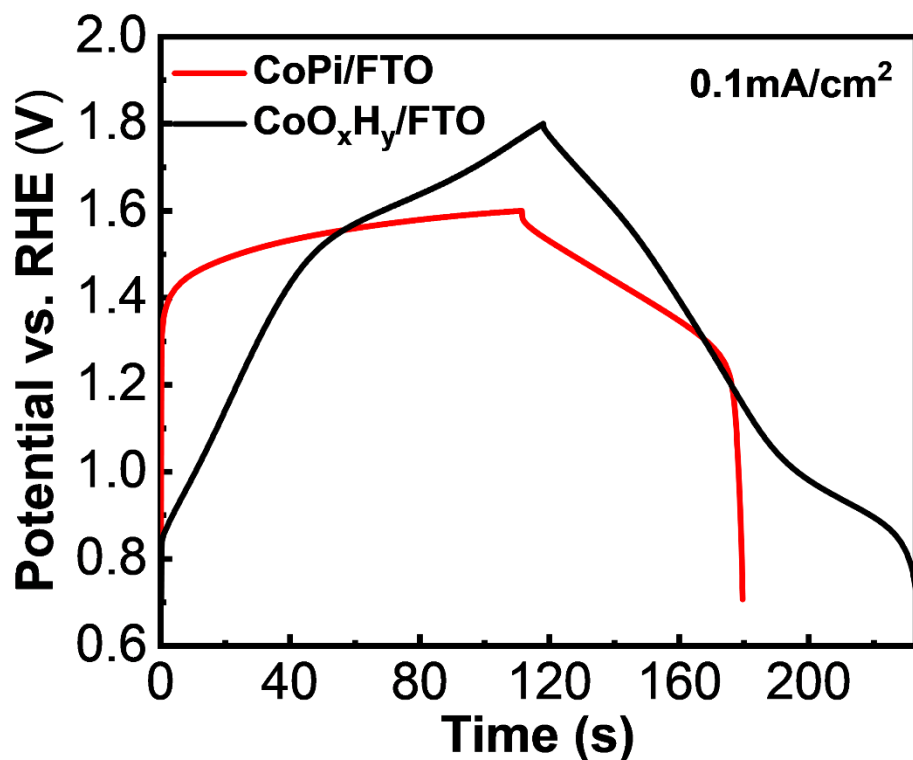
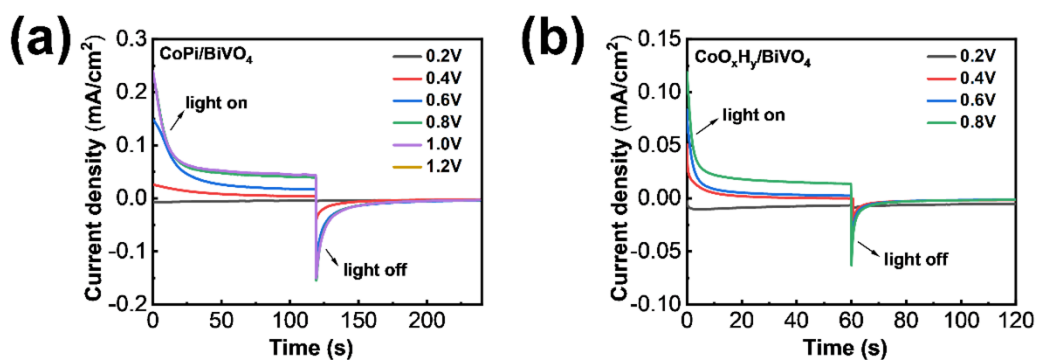


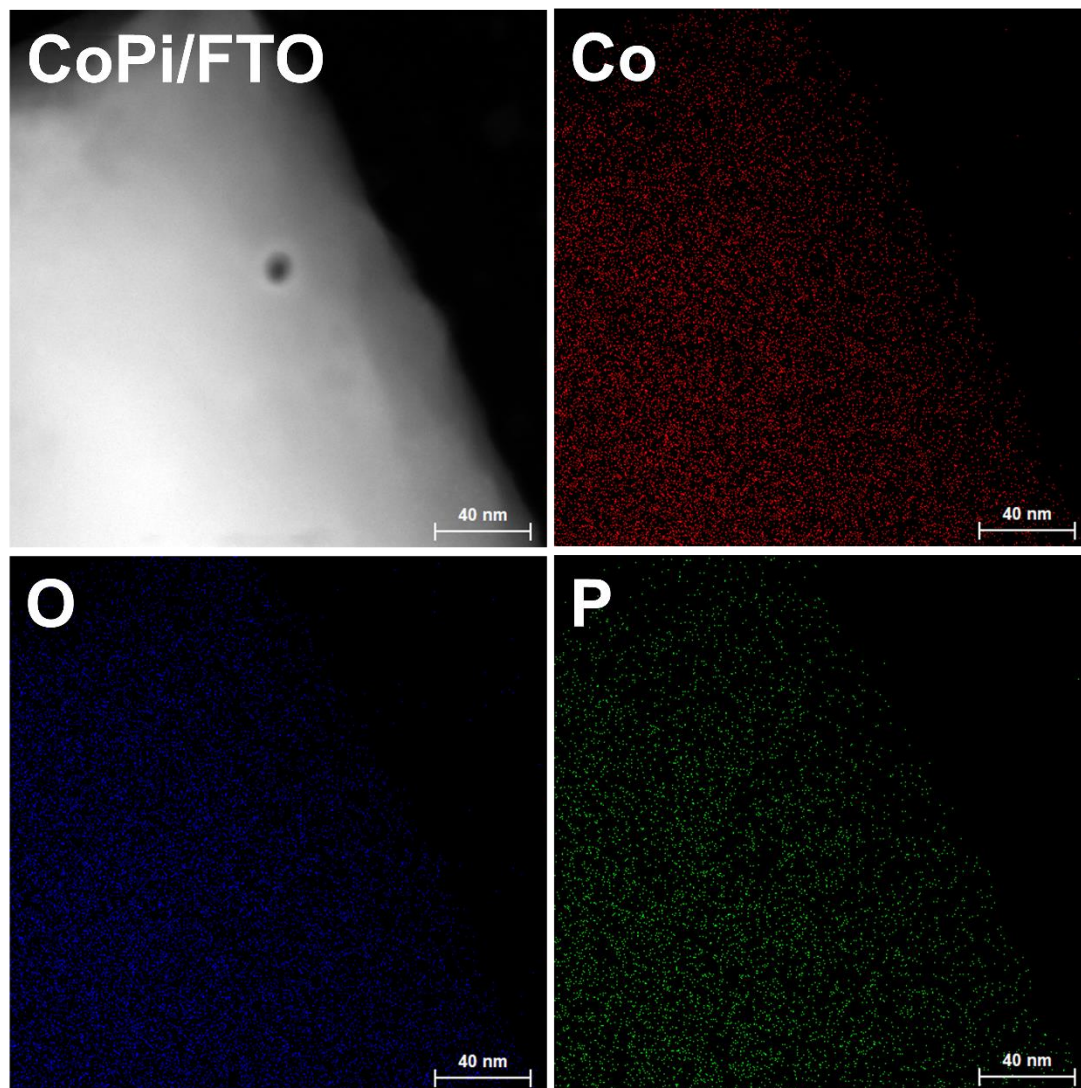
Figure S5. XRD patterns bare BiVO<sub>4</sub>, CoPi/BiVO<sub>4</sub>, CoO<sub>x</sub>H<sub>y</sub>/BiVO<sub>4</sub>.



**Figure S6.** GCD curves of CoPi/FTO in 1M potassium phosphate buffer solution (pH=7) and CoO<sub>x</sub>H<sub>y</sub>/FTO in 0.5 M Na<sub>2</sub>SO<sub>4</sub> aqueous solution, respectively.



**Figure S7.** Current-time curves of CoPi/BiVO<sub>4</sub> in 1M potassium phosphate buffer solution (pH=7) and CoO<sub>x</sub>H<sub>y</sub>/BiVO<sub>4</sub> in 0.5 M Na<sub>2</sub>SO<sub>4</sub> aqueous solution, respectively.



**Figure S8.** Elemental mappings in a dark-field TEM image of CoPi/FTO.

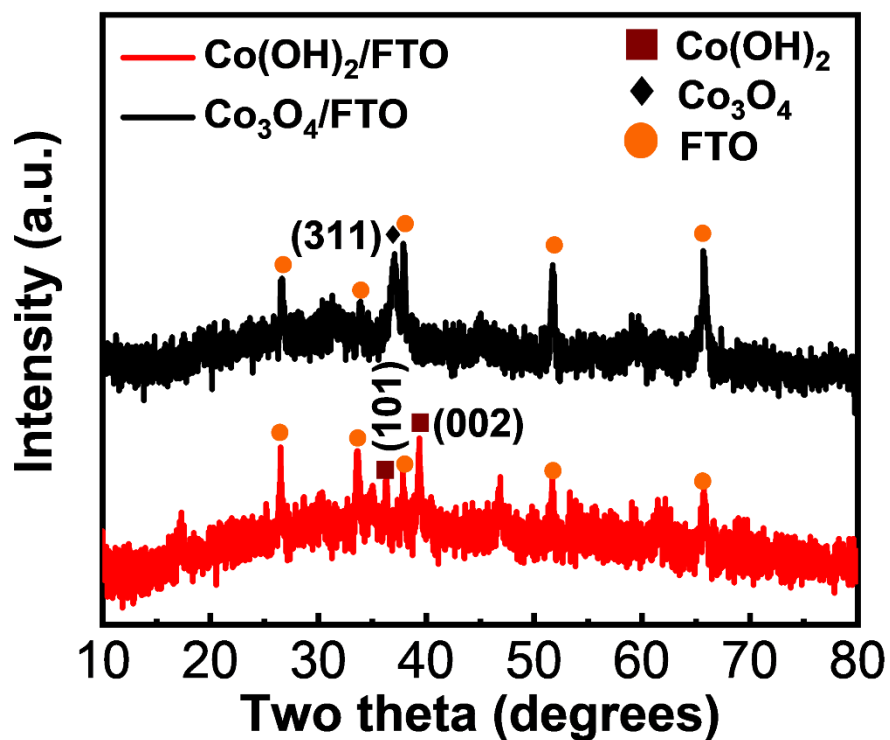


Figure S9. XRD patterns of  $\text{Co}(\text{OH})_2/\text{FTO}$  and  $\text{Co}_3\text{O}_4/\text{FTO}$ .

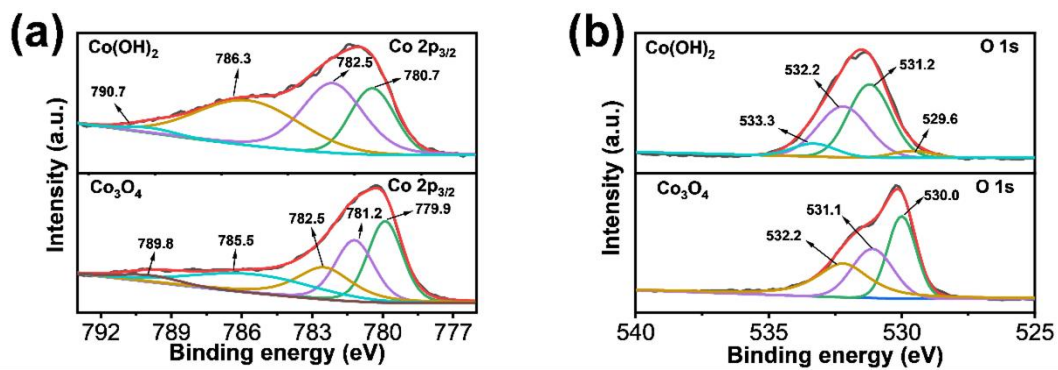
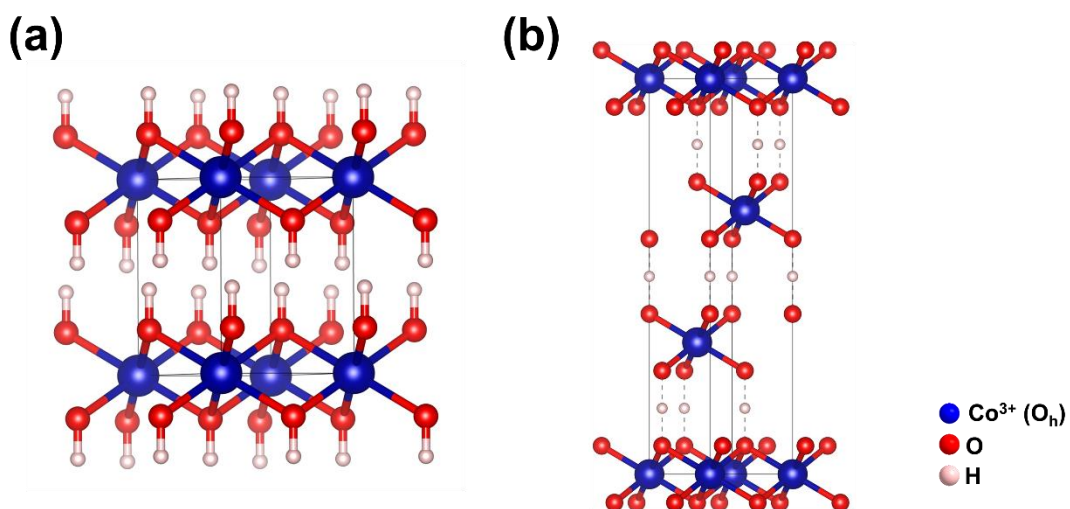
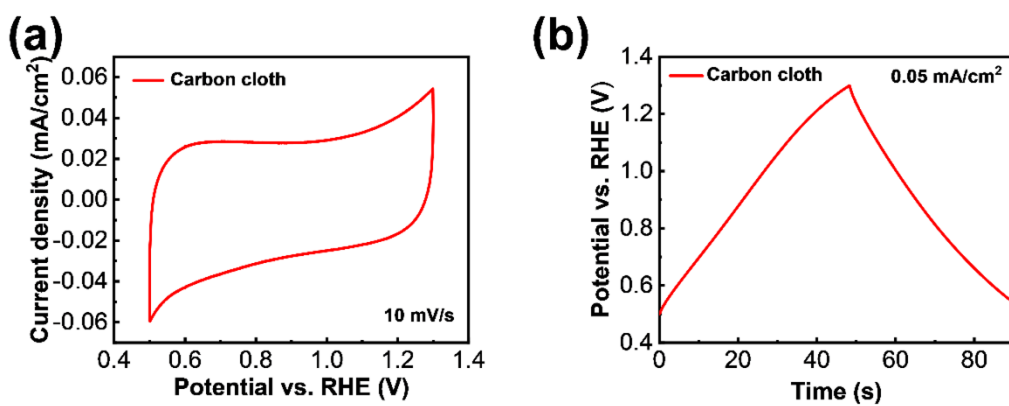


Figure S10. XPS of  $\text{Co}(\text{OH})_2/\text{FTO}$  and  $\text{Co}_3\text{O}_4/\text{FTO}$ .

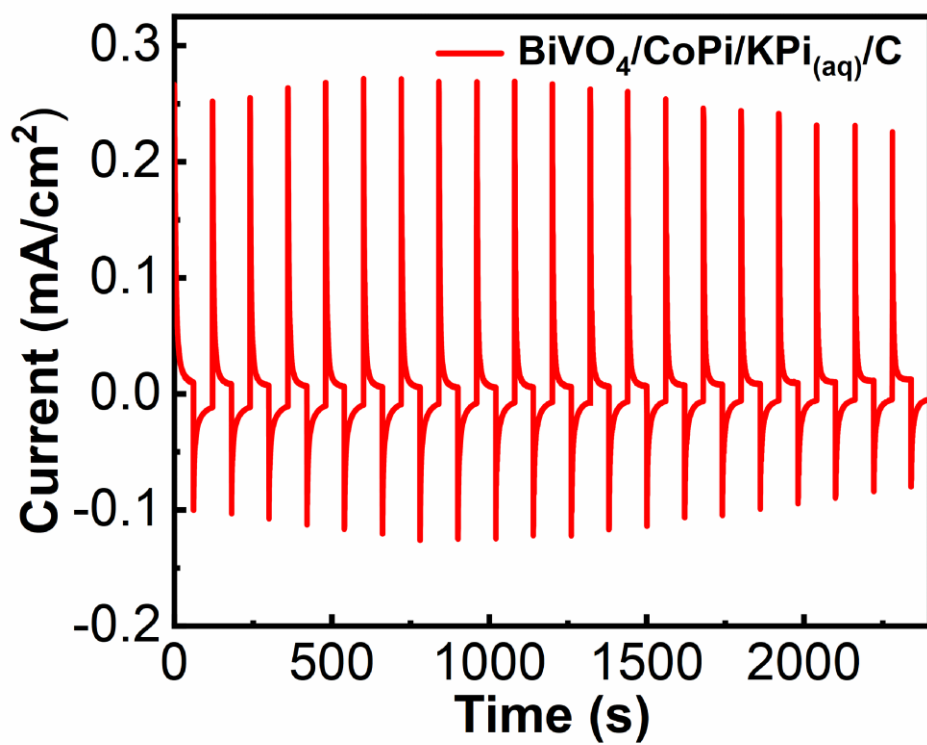




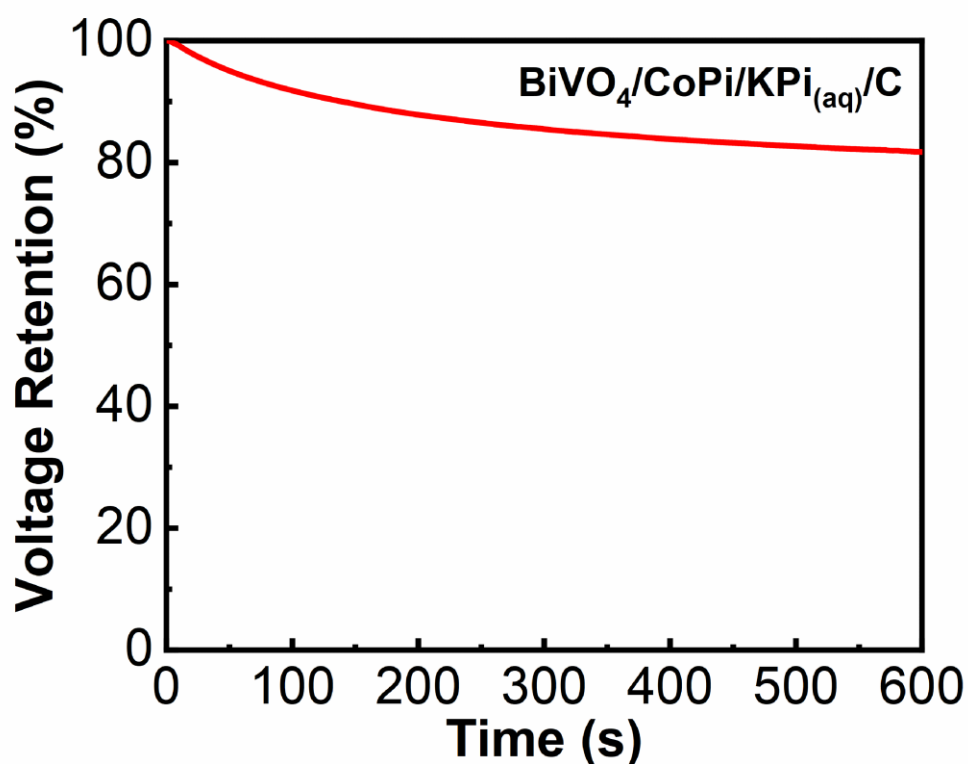
**Figure S11.** Crystal structures of  $\text{Co}(\text{OH})_2$  (a) and  $\text{CoOOH}$  (b).



**Figure S12.** CV curve and GCD curve of a carbon cloth counter electrode in the dark, electrolyte: 1 M potassium phosphate buffer solution (pH=7).



**Figure S13.** Cyclic stability of the BiVO<sub>4</sub>/ CoPi/KPi<sub>(aq)</sub>/C full-cell during photo charge and dark discharge under zero bias.



**Figure S14.** OCP stability of the  $\text{BiVO}_4/\text{CoPi}/\text{KPi}_{(\text{aq})}/\text{C}$  device in the dark.

**Table S1** The output voltage of two-electrode solar rechargeable devices in this study and previous literatures.

	Different configurations of two-electrode devices	Dark output voltage (V)	Ref.
1	$\text{TiO}_2$ -dye-LiI/AC/ Polymer electrolyte/AC/Pt	0.45	[2]
2	$\text{TiO}_2/\text{NiO}/\text{Na}_2\text{SO}_4(\text{aq})/\text{Pt}/\text{Si}$	0.45	[3]
3	Si/Porous Si/Polymer electrolyte/Porous Si	0.55	[4]
4	$\text{BiVO}_4/\text{PbO}_x/\text{NaPi}(\text{aq})/\text{Pt}$	0.65	[5]
5	Si/ $\text{WO}_3/\text{H}_2\text{SO}_4(\text{aq})/\text{C}$	0.50	[6]
6	$\text{BiVO}_4/\text{CoPi}/\text{KPi}_{(\text{aq})}/\text{C}$	0.88	this work

## References

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